



## 1.0 Features

- On-chip tunable voltage-controlled crystal oscillator circuitry (VCXO) allows precise system frequency tuning (pull range typically 300ppm)
- VCXO tuning range: 0-3V
- Uses inexpensive fundamental-mode crystals
- Integrated phase-locked loop (PLL) multiplies VCXO frequency to the higher system frequencies needed
- 5V core supply voltage (contact factory for 3.3V)
- 3.3V / 5V output supply voltage
- Small circuit board footprint (8-pin 0.150" SOIC)
- Custom frequency selections available contact your local AMI Sales Representative for more information

## 2.0 Description

The FS6146 is a monolithic GMOS clock generator IC designed to minimize cost and component count in digital video/audio systems.

At the core of the FS6146 is circuitry that implements a voltage-controlled crystal oscillator when an external resonator is attached. The VCXO allows device frequencies to be precisely adjusted for use in systems that have frequency matching requirements, such as digital satellite receivers.

A high-resolution phase-locked loop generates the output clock frequencies (CLKA and CLKB). These frequencies are phase-locked and frequency-locked to the VCXO frequency.

#### **Figure 1: Pin Configuration** XIN ()16 n/c 15 XOUT n/c VDD 14 n/c ES6146 XTUNE 13 VDDO VSS 12 VSS 11 n/c CLKB OE 7 10 n/c

16-pin (0.150") SOIC

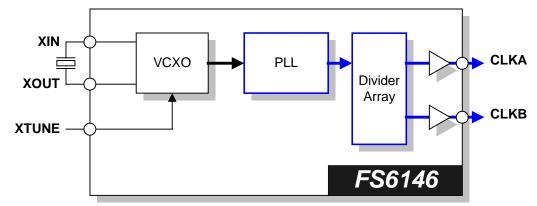
#### Table 1: Crystal / Output Frequencies

| DEVICE    | f <sub>xin</sub> (MHz) | CLKA (MHz) | CLKB (MHz) |
|-----------|------------------------|------------|------------|
| FS6146-01 | 10.000                 | 40.000     | 80.000     |

NOTE: Contact AMI for custom PLL frequencies

#### Figure 2: Block Diagram

CLKA



This document contains information on a preproduction product. Specifications and information herein are subject to change without notice.

9 n/c



#### Table 2: Pin Descriptions

Key: AI = Analog Input; AO = Analog Output; DI = Digital Input; DI<sup>U</sup> = Input with Internal Pull-Up; DI<sub>D</sub> = Input with Internal Pull-Down; DIO = Digital Input/Output; DI-3 = Three-Level Digital Input, DO = Digital Output; P = Power/Ground; # = Active Low pin

| PIN | TYPE            | NAME        | DESCRIPTION   |
|-----|-----------------|-------------|---|
| 1   | AI              | XIN         | VCXO Crystal Feedback                                   |
| 2   | AO              | XOUT / FREF | VCXO Crystal Drive / External Reference Clock Input     |
| 3   | Р               | VDD         | Core Power Supply                                       |
| 4   | AI              | XTUNE       | VCXO Tune Input   |
| 5   | Р               | VSS         | Ground  |
| 6   | -               | N/C         | No Connection   |
| 7   | DI <sup>U</sup> | OE          | Output Enable   |
| 8   | DO              | CLKA        | Clock Output "A"  |
| 9   | -               | N/C         | No Connection   |
| 10  | -               | N/C         | No Connection   |
| 11  | DO              | CLKB        | Clock Output "B"  |
| 12  | Р               | VSS         | Ground  |
| 13  | Р               | VDDO <      | Output Power Supply (must be less than or equal to VDD) |
| 14  | -               | N/C         | No Connection   |
| 15  | -               | N/C         | No Connection   |
| 16  | -               | N/C         | No Connection   |

# 3.0 Functional Block Description

#### 3.1 Phase-Locked Loop (PLL)

The on-chip PLL is a standard frequency- and phaselocked loop architecture. The PLL multiplies the reference oscillator to the desired frequency by a ratio of integers. The frequency multiplication is exact with a zero synthesis error.

#### 3.2 Voltage-Controlled Crystal Oscillator (VCXO)

The VCXO provides a tunable, low-jitter frequency reference for the rest of the FS6146 system components. Loading capacitance for the crystal is internal to the FS6146. No external components (other than the crystal resonator itself) are required for operation of the VCXO.

Continuous fine-tuning of the VCXO frequency is accomplished by varying the voltage on the XTUNE pin.

The oscillator operates the crystal resonator in the parallel-resonant mode. Crystal warping, or the "pulling" of the crystal oscillation frequency, is accomplished by altering the effective load capacitance presented to the crystal by the oscillator circuit. The actual amount that changing the load capacitance alters the oscillator frequency will be dependent on the characteristics of the crystal as well as the oscillator circuit itself.

Specifically, the motional capacitance of the crystal (usually referred to by crystal manufacturers as  $C_1$ ), the static capacitance of the crystal ( $C_0$ ), and the load capacitance ( $C_L$ ) of the oscillator determine the "warping" or "pulling" capability of the crystal in the oscillator circuit.

A simple formula to obtain the warping capability of a crystal oscillator is:

$$\Delta f(ppm) = \frac{C_1 \times (C_{L2} - C_{L1}) \times 10^6}{2 \times (C_0 + C_{L2}) \times (C_0 + C_{L1})}$$

where  $C_{L1}$  and  $C_{L2}$  are the two extremes of the applied load capacitance.

EXAMPLE: A crystal with the following parameters is used. With  $C_1 = 0.02pF$ ,  $C_0 = 5pF$ ,  $C_{L1} = 10pF$ , and  $C_{L2} = 22.66pF$ , the tuning range is

$$\Delta f = \frac{0.02 \times (22.66 - 10) \times 10^6}{2 \times (5 + 22.66) \times (5 + 10)} = 305 \, ppm \,.$$

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## 4.0 **Electrical Specifications**

#### **Table 3: Absolute Maximum Ratings**

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These conditions represent a stress rating only, and functional operation of the device at these or any other conditions above the operational limits noted in this specification is not implied. Exposure to maximum rating conditions for extended conditions may affect device performance, functionality, and reliability.

| renetionality, and renability.   |                         | $\land$ $\land$ $\land$ |                      |       |
|--|-------------------------|-------------------------|----------------------|-------|
| PARAMETER  | SYMBOL                  | MIN.                    | MAX.                 | UNITS |
| Supply Voltage (V <sub>SS</sub> = ground)  | V <sub>D0</sub>         | V <sub>ss</sub> -0.5    | 7                    | V     |
| Input Voltage, dc  | VI                      | V <sub>ss</sub> -0.5    | √ <sub>DD</sub> +0.5 | V     |
| Output Voltage, dc   | $\langle v_{o} \rangle$ | V <sub>SS</sub> -0.5    | V <sub>DD</sub> +0.5 | V     |
| Input Clamp Current, dc (V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>DD</sub> )  | IK T                    | -50                     | 50                   | mA    |
| Output Clamp Current, dc (V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>DD</sub> ) |                         | ( )-50                  | 50                   | mA    |
| Storage Temperature Range (non-condensing)   | Ts                      | _65                     | 150                  | °C    |
| Ambient Temperature Range, Under Bias  | T T                     | -55                     | 125                  | °C    |
| Junction Temperature   |                         |                         | 125                  | °C    |
| Lead Temperature (soldering, 10s)  |                         |                         | 260                  | °C    |
| Input Static Discharge Voltage Protection (MIL-STD 883E, Method 30                 | 5.7)                    |                         | 2                    | kV    |



#### CAUTION: ELECTROSTATIC SENSITIVE DEVICE

Permanent damage resulting in a loss of functionality or performance may occur if this device is subjected to a high-energy electrostatic discharge.

## Table 4: Operating Conditions

| PARAMETER                              | SYMBOL               | CONDITIONS/DESCRIPTION | MIN. | TYP. | MAX. | UNITS |
|--|----------------------|------------------------|------|------|------|-------|
| Supply Voltage                         | V <sub>DD</sub>      | 5V ± 5%                | 4.75 | 5    | 5.25 | V     |
| Ambient Operating Temperature Range    | T <sub>A</sub>       |                        | 0    |      | 70   | °C    |
| Crystal Resonator Frequency            | f <sub>XTAL</sub>    | Fundamental Mode       | 5    | 13.5 | 18   | MHz   |
| Crystal Resonator Motional Capacitance | C <sub>1(xtal)</sub> | AT cut                 |      | 25   |      | fF    |
| Crystal Loading Capacitance            | C <sub>L(xtal)</sub> | AT cut                 |      | 14   |      | pF    |



#### **Table 5: DC Electrical Specifications**

Unless otherwise stated,  $V_{DD} = 5V \pm 10\%$ , no load on any output, and ambient temperature range  $T_A = 0^{\circ}C$  to 70°C. Parameters denoted with an asterisk (\*) represent nominal characterization data and are not production tested to any specific limits. Where given, MIN and MAX characterization data are  $\pm 3\sigma$  from typical. Negative currents indicate current flows out of the device.

| PARAMETER                                       | SYMBOL               | CONDITIONS/DESCRIPTION  | MIN               | TYP. | MAX. | UNITS |
|---|----------------------|---|-------------------|------|------|-------|
| Overall   |                      |   | $\langle \rangle$ |      |      |       |
| Supply Current, Dynamic, with Loaded<br>Outputs | I <sub>DD</sub>      | f <sub>XTAL</sub> = 13.5MHz; C <sub>L</sub> = 10pF                                    |                   | 20   |      | mA    |
| Voltage Controlled Crystal Oscillator - VDI     | D=5.0V               |   | (0                | 5    |      |       |
| Crystal Loading Capacitance                     | C <sub>L(xtal)</sub> | As seen by a crystal connected to XIN and XOUT (@ $V_{XTUNE} = 1.65V$ )               |                   | 9 14 |      | pF    |
| Crystal Resonator Motional Capacitance          | C <sub>1(xtal)</sub> | AT cut  | $\bigcirc$        | 25   |      | fF    |
| VCXO Tuning Range                               |                      | f <sub>XTAL</sub> = 13.5MHz; C <sub>L(xtal)</sub> = 14pF; C <sub>1(xtal)</sub> = 25fF |                   | 300  |      | ppm   |
| VCXO Tuning Characteristic                      |                      | Note: positive $\Delta F$ for positive $\Delta V$                                     | $\mathcal{D}$     | 100  |      | ppm/V |
| Crystal Drive Level                             |                      | $R_{XTAL}=20\Omega; C_{L(xtal)}=14pF$   |                   | 200  |      | uW    |
| Clock Outputs (CLKA, CLKB) - VDDO=3.3           | 1                    |   |                   |      |      |       |
| High-Level Output Source Current *              | І <sub>он</sub>      | (VQ≠2.0V ())  |                   | -40  |      | mA    |
| Low-Level Output Sink Current *                 | lø_ /                | V <sub>0</sub> =0.4V  |                   | 17   |      | mA    |
| Output Impodonoo *                              | ZOH                  | $V_{O} = 0.1 V_{DD}$ ; output driving high  |                   | 25   |      | Ω     |
| Output Impedance *                              | Z <sub>OL</sub>      | $V_{o} = 0.1 V_{DD}$ ; output driving low   |                   | 25   |      | 52    |
| Short Circuit Source Current *                  | IOSH                 | $V_0 = 0V$ ; shorted for 30s, max.  |                   | -55  |      | mA    |
| Short Circuit Sink Current *                    | I <sub>OSL</sub>     | $V_{0} = 5V$ ; shorted for 30s, max.  |                   | 55   |      | mA    |

## Table 6: AC Timing Specifications

Unless otherwise stated,  $V_{DD} = 5V \pm 10\%$ , no load on any output, and ambient temperature range  $T_A = 0^\circ$ C to 70°C. Parameters denoted with an asterisk (\*) represent nominal characterization data and are not production tested to any specific limits. Where given, MIN and MAX characterization data are  $\pm 3\sigma$  from typical.

| PARAMETER                                | SYMBOL               | CONDITIONS/DESCRIPTION   | CLOCK<br>(MHz) | MIN. | TYP. | MAX. | UNITS |
|--|----------------------|--|----------------|------|------|------|-------|
| Overall                                  | $\heartsuit$         |  |                |      |      |      |       |
| VCXO Stabilization Time *                | t <sub>VCXOSTB</sub> | From power valid   |                |      | 10   |      | ms    |
| PLL Stabilization Time *                 | t <sub>PLLSTB</sub>  | From VCXO stable   |                |      | 500  |      | us    |
| Output Frequency Synthesis Error         |                      | (unless otherwise noted in Frequency Table)  | 1              |      |      | 0    | ppm   |
| Clock Output (CLK)                       |                      |  |                |      |      |      |       |
| Duty Cycle *                             |                      | Ratio of high pulse width (as measured from rising edge to next falling edge at $V_{\text{DD}}\!/2)$ to one clock period |                | 45   |      | 55   | %     |
| Jitter, Period (peak-peak) *             | $t_{j(\Delta P)}$    | From rising edge to next rising edge at $V_{DD}/2$ , $C_L = 10 pF$   |                |      | 300  |      | ps    |
| Jitter, Long Term ( $\sigma_y(\tau)$ ) * | $t_{j(LT)}$          | From 0-500 $\mu$ s at V <sub>DD</sub> /2, C <sub>L</sub> = 10pF compared to ideal clock source                           |                |      | 150  |      | ps    |
| Rise Time *                              | tr                   | $V_{\text{DD}}$ = 5V; $V_{\text{O}}$ = 0.5V to 4.5V; $C_{\text{L}}$ = 10pF   |                |      |      |      | ns    |
| Fall Time *                              | t <sub>f</sub>       | $V_{DD}$ = 5V; $V_{O}$ = 4.5V to 0.5V; $C_{L}$ = 10pF  |                |      |      |      | ns    |

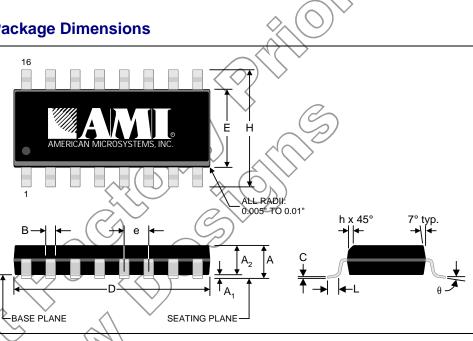




# 5.0 Package Information

#### Table 7: 16-pin SOIC (0.150") Package Dimensions

|    | DIMENSIONS |        |        |       |  |  |  |
|----|------------|--------|--------|-------|--|--|--|
|    | INC        | HES    | MILLIM | ETERS |  |  |  |
|    | MIN.       | MAX.   | MIN.   | MAX.  |  |  |  |
| А  | 0.061      | 0.068  | 1.55   | 1.73  |  |  |  |
| A1 | 0.004      | 0.0098 | 0.102  | 0.249 |  |  |  |
| A2 | 0.055      | 0.061  | 1.40   | 1.55  |  |  |  |
| В  | 0.013      | 0.019  | 0.33   | 0.49  |  |  |  |
| С  | 0.0075     | 0.0098 | 0.191  | 0.249 |  |  |  |
| D  | 0.386      | 0.393  | 9.80   | 9.98  |  |  |  |
| Е  | 0.150      | 0.157  | 3.81   | 3.99  |  |  |  |
| е  | 0.050      | BSC    | 1.27   | BSC   |  |  |  |
| Н  | 0.230      | 0.244  | 5.84   | 6.20  |  |  |  |
| h  | 0.010      | 0.016  | 0.25   | 0.41  |  |  |  |
| L  | 0.016      | 0.035  | 0.41   | 0.89  |  |  |  |
| Θ  | 0°         | 8°     | 0°     | 8°    |  |  |  |



# Table 8: 16-pin SOIC (0.150") Package Characteristics

| PARAMETER   | SYMBOL          | CONDITIONS/DESCRIPTION        | TYP. | UNITS |
|---|-----------------|-------------------------------|------|-------|
| Thermal Impedance, Junction to Free-Air<br>16-pin 0.150" SOIC | $\Theta_{JA}$   | Air flow = 0 m/s              | 109  | °C/W  |
| Lead Inductance, Self   | 1               | Corner lead                   | 4.0  | nH    |
| Lead inductance, Sen  | L <sub>11</sub> | Center lead                   | 3.0  | пп    |
| Lead Inductance, Mutual                                       | L <sub>12</sub> | Any lead to any adjacent lead | 0.4  | nH    |
| Lead Capacitance, Bulk  | C <sub>11</sub> | Any lead to V <sub>SS</sub>   | 0.5  | pF    |



## 6.0 Ordering Information

#### **Table 9: Device Ordering Codes**

| ORDERING CODE | DEVICE NUMBER | PACKAGE TYPE                                   | OPERATING<br>TEMPERATURE RANGE | SHIPPING<br>CONFIGURATION |
|---------------|---------------|--|--------------------------------|---------------------------|
| 11640-823     | FS6146-01     | 8-pin (0.150") SOIC<br>(Small Outline Package) | 0°C to 70°C (Commercial)       | Tape and Reel             |
| 11640-833     | FS6146-01     | 8-pin (0.150") SOIC<br>(Small Outline Package) | 0°C to 70°C (Commercial)       | Tubes                     |

### 7.0 Revision Information

| DATE    | PAGE | DESCRIPTION                 |
|---------|------|-----------------------------|
| 4/26/00 | 2    | Fixed formatting errors     |
| 7/31/00 | 3    | Changed "5V±10%" to "5V±5%" |
|         |      |                             |

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